

MSKSEMI 美森科

SEMICONDUCTOR



ESD



TVS



TSS



MOV



GDT



PLED

GBU12005-MS THRU GBU1210-MS

Product specification

VOLTAGE RANGE: 50 - 1000V
CURRENT: 12 A

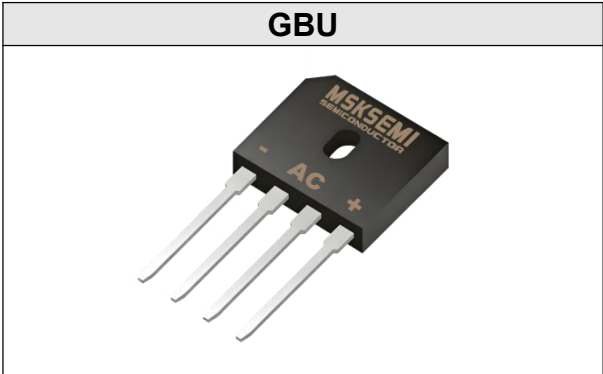
FEATURES

- The plastic package carries Underwriters Laboratory Flammability Classification 94V-0
- dea for printed circuit board
- Glass passivated junction chip
- Low reverse leakage
- High forward surge current capability
- High temperature soldering guaranteed
260 °C/10 seconds at terminals

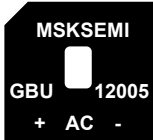
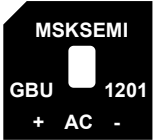
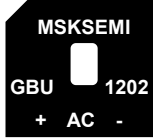
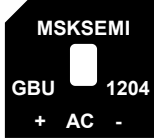
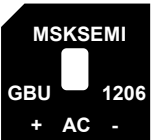
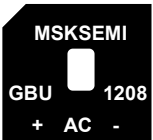
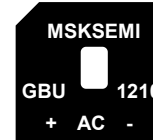
Mechanical Data

Case : Molded plastic body
Terminals : Solder plated, solderable per MIL-STD-750,Method 2026
Polarity : Polarity symbol marking on body
Mounting Position : Any

REFERENCE NEWS



Marking

GBU 12005-MS	GBU 1201-MS	GBU 1202-MS	GBU 1204-MS
			
GBU1206-MS	GBU1208-MS	GBU1210-MS	
			

MAXIMUM RATINGS AND ELECTRICAL CHARACTERISTICS

Ratings at 25°C ambient temperature unless otherwise specified. Single phase half-wave 60Hz, resistive or inductive load, for capacitive load current derate by 20%.

Parameter	SYMBOLS	GBU12005 -MS	GBU1201 -MS	GBU1202 -MS	GBU1204 -MS	GBU1206 -MS	GBU1208 -MS	GBU1210 -MS	UNITS
Maximum repetitive peak reverse voltage	V _{RRM}	50	100	200	400	600	800	1000	V
Maximum RMS voltage	V _{RMS}	35	70	140	280	420	560	700	V
Maximum DC blocking voltage	V _{DC}	50	100	200	400	600	800	1000	V
Maximum average forward rectified current with heatsink	I _(AV)	12.0							A
Peak forward surge current, 8.3ms single half sine-wave superimposed on rated load	I _{FSM}	240.0							A
Rating for fusing (t=8.3ms, Ta=25°C)	I ² _t	239							A ² s
Maximum instantaneous forward voltage at 12.0A	V _F	1.10							V
Maximum DC reverse current at Ta=25°C rated DC blocking voltage Ta=125°C	I _R	2.0 200							uA
Typical junction capacitance (Note 1)	C _J	58.0							pF
Typical thermal resistance	R _{QA}	25.0							°C/W
Operating junction and storage temperature range	T _J ,T _{STG}	-55 to +150							°C

Note: 1.Measured at 1MHz and applied reverse voltage of 4.0V D.C.

RATING AND CHARACTERISTIC CURVES (GBU12005-MS THRU GBU1210-MS)

FIG. 1- DERATING CURVE OUTPUT RECTIFIED CURRENT

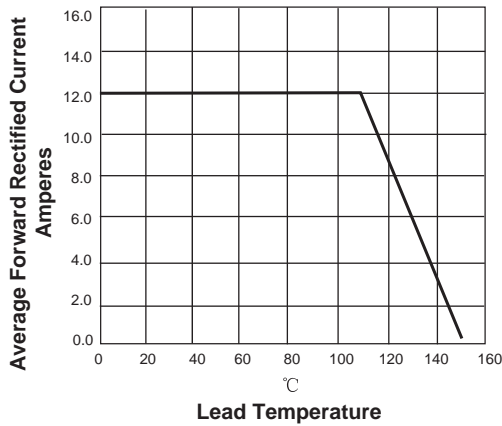


FIG. 2-MAXIMUM NON-REPETITIVE PEAK FORWARD SURGE CURRENT PER LEG

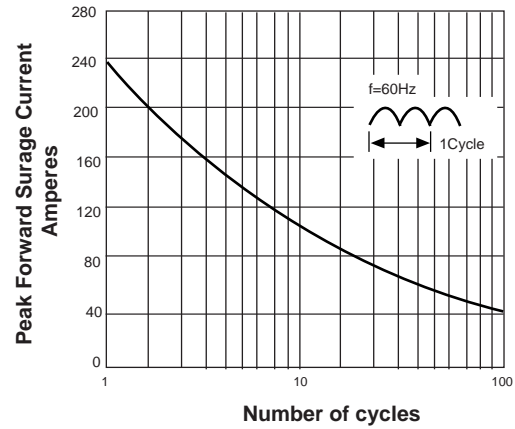


FIG. 3-TYPICAL FORWARD VOLTAGE CHARACTERISTICS

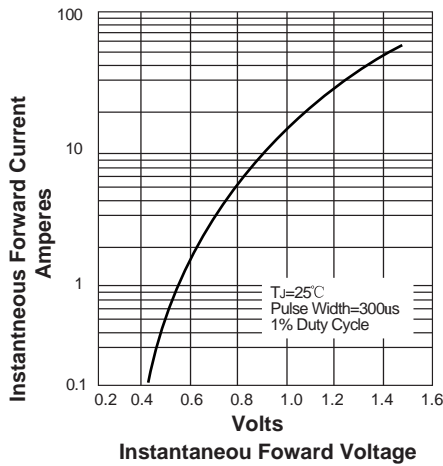
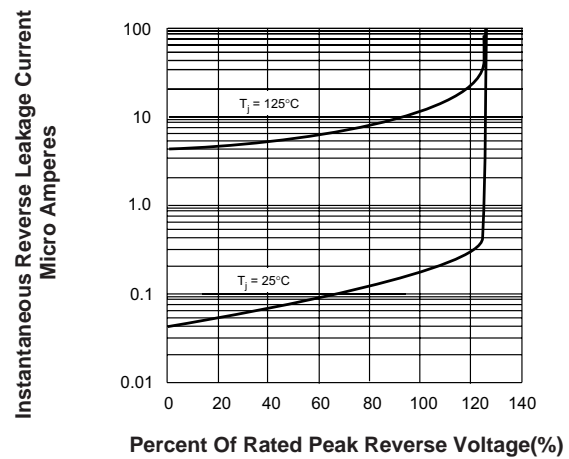
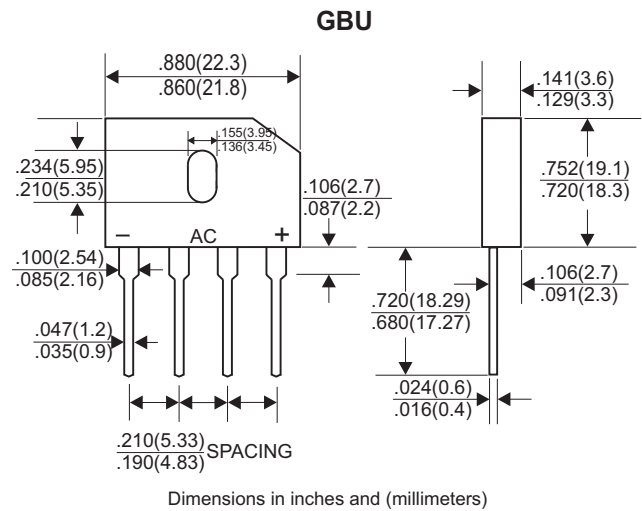


FIG. 4-TYPICAL REVERSE LEAKAGE CHARACTERISTICS



PACKAGE MECHANICAL DATA



REELSPECIFICATION

P/N	PKG	QTY
GBU12005-MS THRU GBU1210-MS	GBU	500

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